

Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY

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	V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
Channel-1	30	0.023 at V _{GS} = 10 V	7.0
		0.032 at V _{GS} = 4.5 V	5.6
Channel-2		0.020 at V _{GS} = 10 V	7.4
		0.027 at V _{GS} = 4.5 V	6.4

SCHOTTKY PRODUCT SUMMARY

V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)
30	0.40 V at 1.0 A	2.0

FEATURES

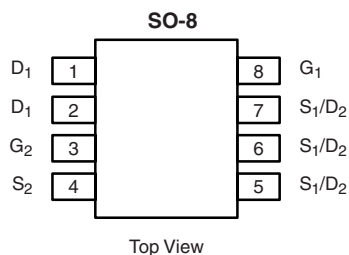
- LITTLE FOOT® Plus Integrated Schottky
- 100 % R_g Tested

APPLICATIONS

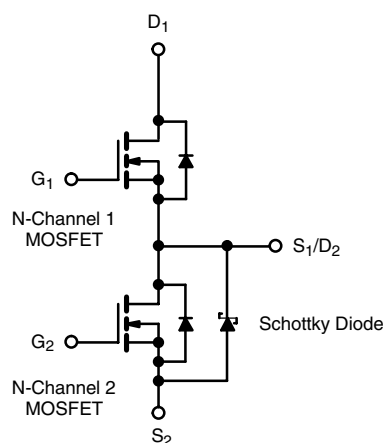
- Logic DC/DC
- Notebook PC



RoHS
COMPLIANT



Ordering Information: Si4914DY-T1-E3 (Lead (Pb)-free)



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	Channel-1		Channel-2		Unit
			10 sec	Steady State	10 sec	Steady State	
Drain-Source Voltage		V _{DS}	30				V
Gate-Source Voltage		V _{GS}	20				
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	7.0	5.5	7.4	5.7	A
	T _A = 70 °C		5.6	4.3	6	4.5	
Pulsed Drain Current		I _{DM}	40		40		
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	1.0	1.8	0.95	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	13		15		
Avalanche Energy		E _{AS}	8.45		11		mJ
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	1.9	1.1	2.0	1.16	W
	T _A = 70 °C		1.2	0.71	1.3	0.74	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150				°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Channel-1		Channel-2		Unit
		Typ	Max	Typ	Max	
Maximum Junction-to-Ambient ^a	R _{thJA}	52	65	47	60	°C/W
		90	112	85	107	
Maximum Junction-to-Foot (Drain)	R _{thJF}	30	38	28	35	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

MOSFET SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min	Typ ^a	Max	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch-1	1.0		2.5	V
			Ch-2	1.0		2.5	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V	Ch-1			100	nA
			Ch-2			100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1			1	μA
			Ch-2			500	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 85 °C	Ch-1			0.015	mA
			Ch-2			20	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	Ch-1	20			A
			Ch-2	20			
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 7.0 A	Ch-1		0.019	0.023	Ω
		V _{GS} = 10 V, I _D = 7.4 A	Ch-2		0.016	0.020	
		V _{GS} = 4.5 V, I _D = 5.6 A	Ch-1		0.026	0.032	
		V _{GS} = 4.5 V, I _D = 6.4 A	Ch-2		0.022	0.027	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7.0 A	Ch-1		19		S
		V _{DS} = 15 V, I _D = 7.4 A	Ch-2		22		
Diode Forward Voltage ^b	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V	Ch-1		0.75	1.1	V
		I _S = 1 A, V _{GS} = 0 V	Ch-2		0.36	0.40	
Dynamic ^a							
Total Gate Charge	Q _g	Channel-1 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 7.0 A	Ch-1		5.6	8.5	nC
Gate-Source Charge	Q _{gs}		Ch-2		7.3	11	
		Channel-2 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 7.4 A	Ch-1		2.3		
Ch-2			2.8				
Gate-Drain Charge	Q _{gd}	Ch-1		1.7			
		Ch-2		2.2			
Gate Resistance	R _g		Ch-1	0.5	2.3	3.6	Ω
			Ch-2	0.5	1.6	2.5	
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 6 Ω	Ch-1		6	10	ns
Rise Time	t _r		Ch-2		7	11	
			Ch-1		13	20	
Turn-Off Delay Time	t _{d(off)}		Ch-2		13	20	
		Channel-2 V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 6 Ω	Ch-1		27	40	
Fall Time	t _f	Ch-2		35	53		
		Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.3 A, di/dt = 100 A/μs	Ch-1		30
I _F = 2.2 A, di/dt = 100 μA/μs	Ch-2				30	50	

Notes:

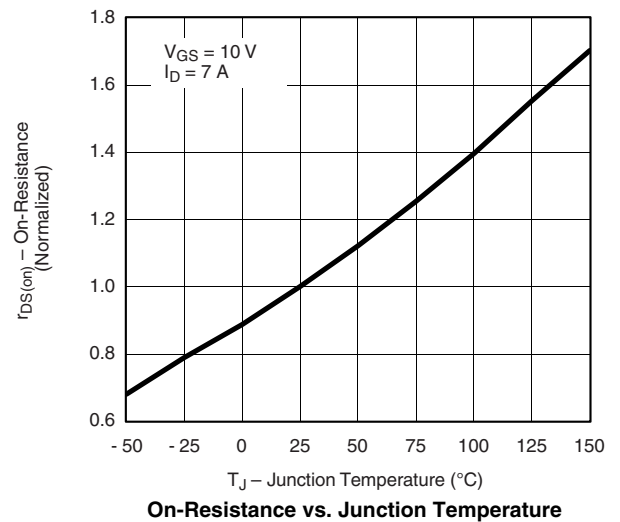
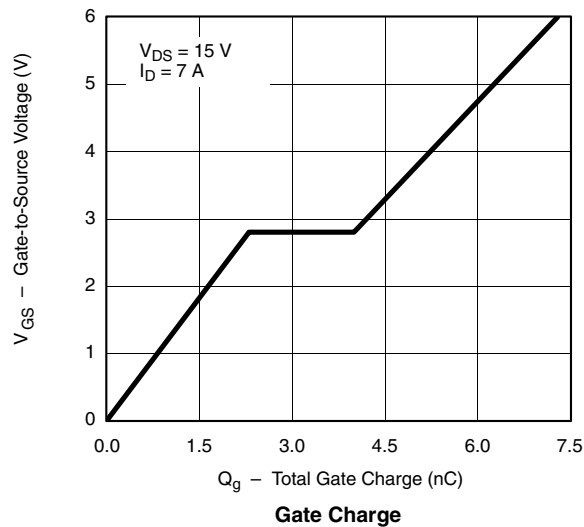
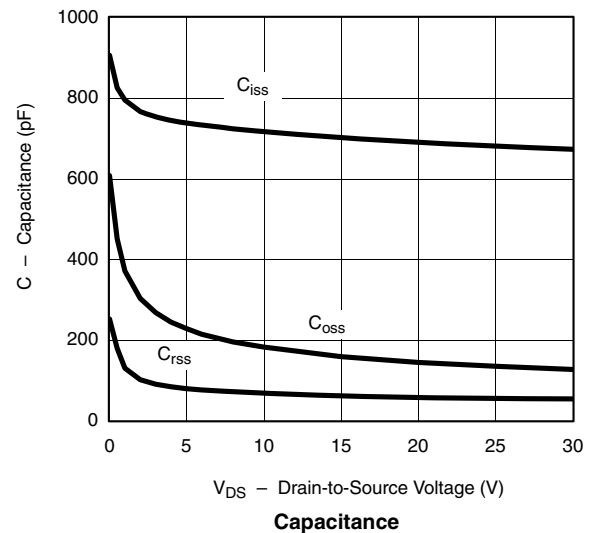
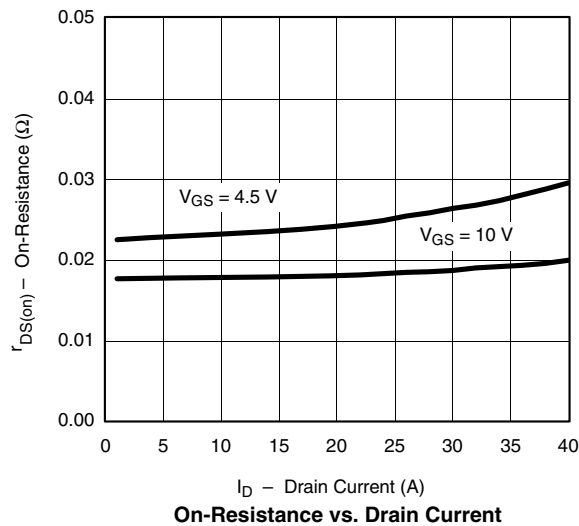
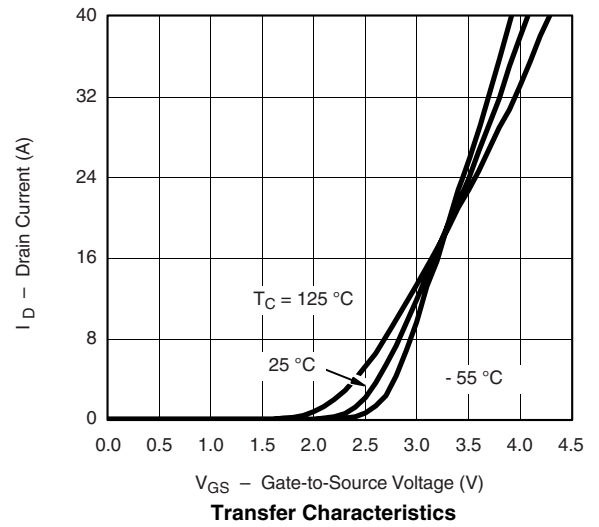
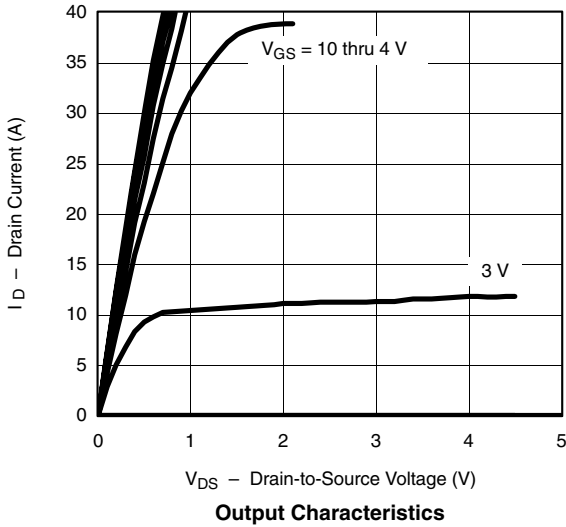
a. Guaranteed by design, not subject to production testing.

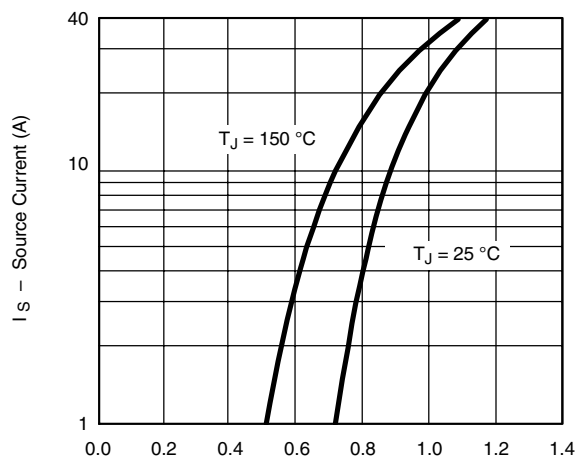
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Forward Voltage Drop	V_F	$I_F = 1.0\text{ A}$			0.36	0.40	V
		$I_F = 1.0\text{ A}$, $T_J = 150\text{ }^{\circ}\text{C}$			0.27	0.31	
Maximum Reverse Leakage Current	I_{rm}	$V_r = 30\text{ V}$			0.008	0.50	mA
		$V_r = 30\text{ V}$, $T_J = 100\text{ }^{\circ}\text{C}$			3.5	10	
		$V_r = -30\text{ V}$, $T_J = 125\text{ }^{\circ}\text{C}$			10	100	
Junction Capacitance	C_T	$V_r = 10\text{ V}$			58		pF

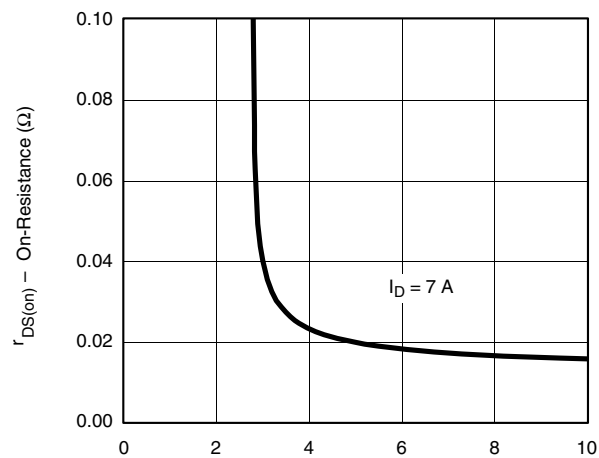
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless noted

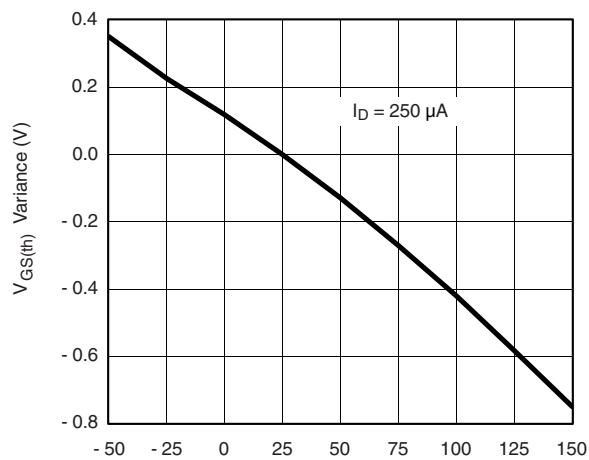


CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless noted

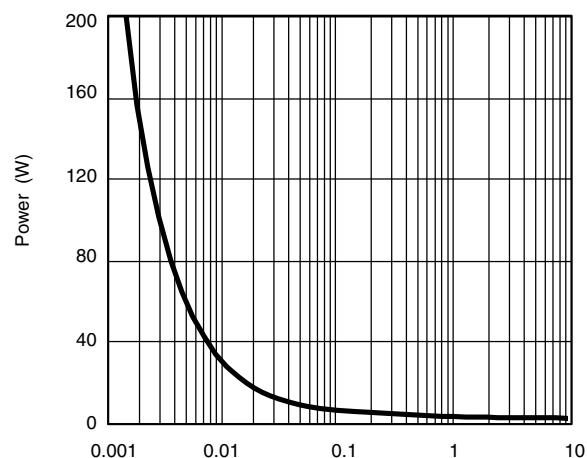
Source-Drain Diode Forward Voltage



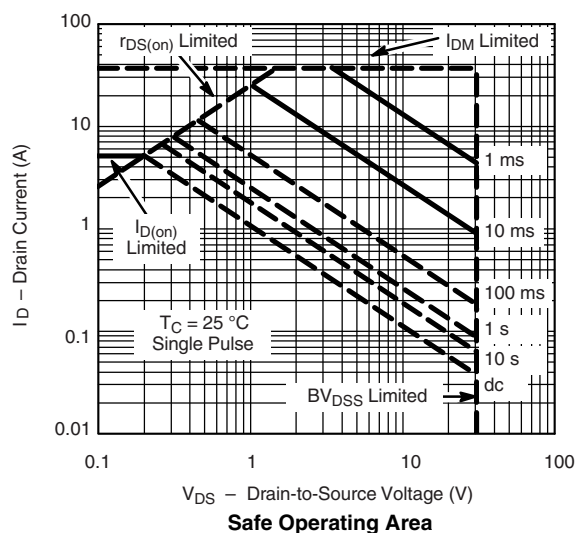
On-Resistance vs. Gate-to-Source Voltage



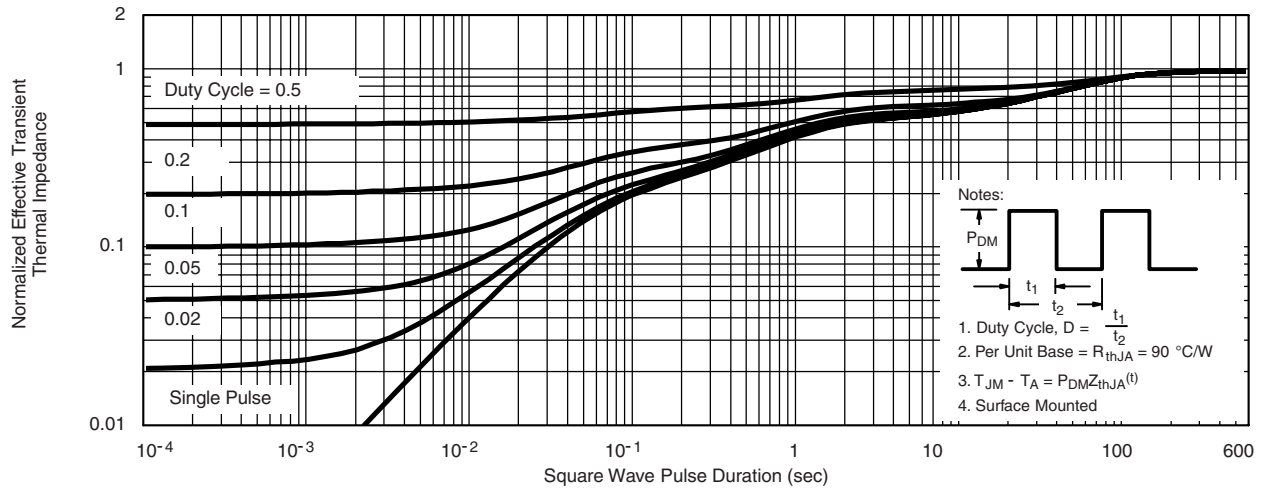
Threshold Voltage



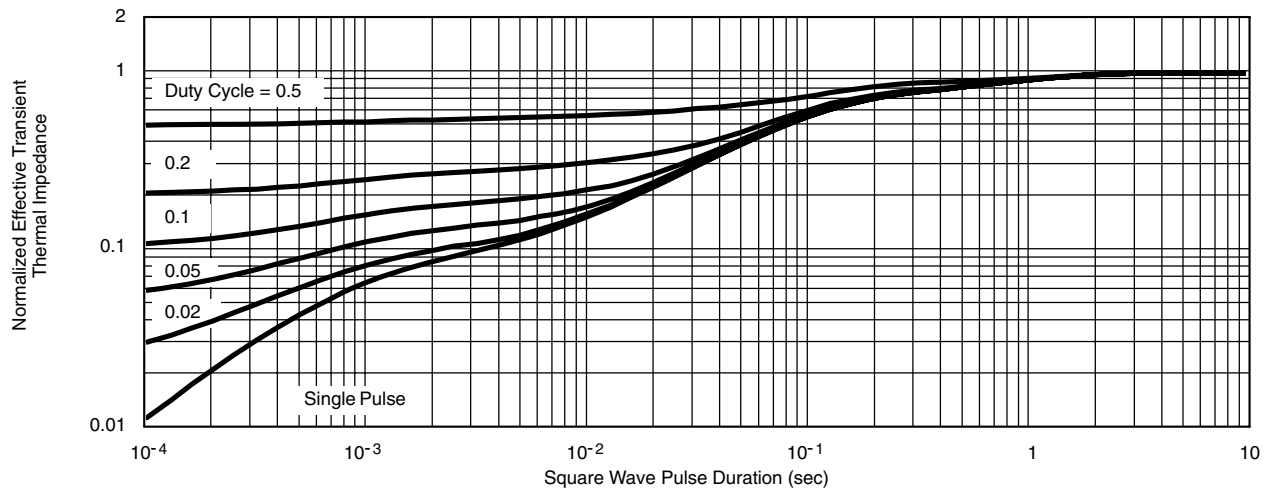
Single Pulse Power, Junction-to-Ambient



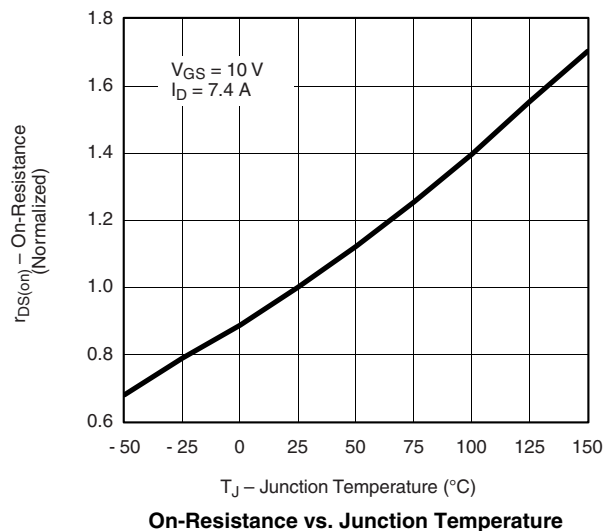
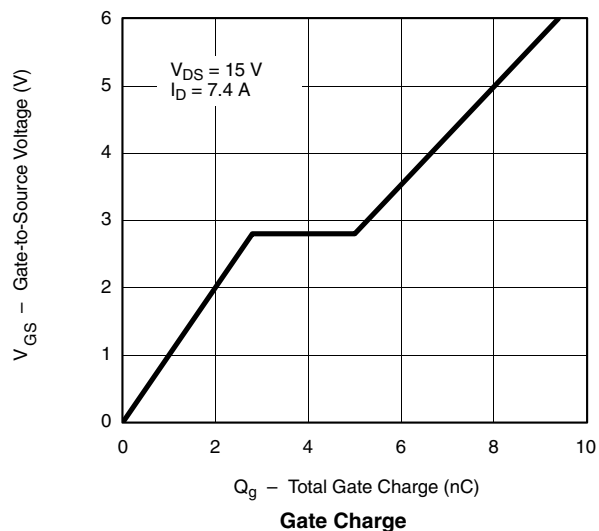
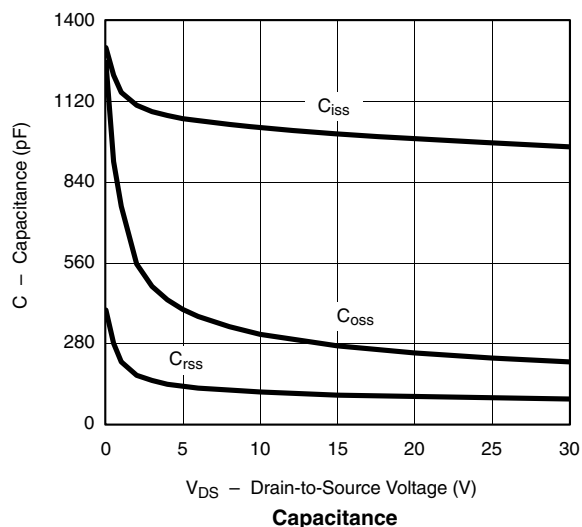
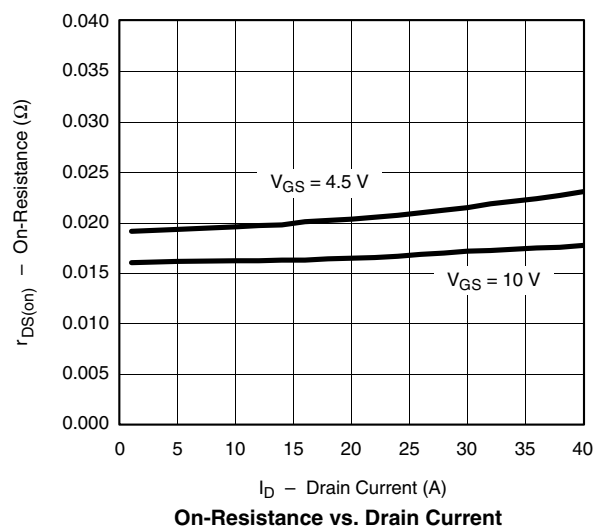
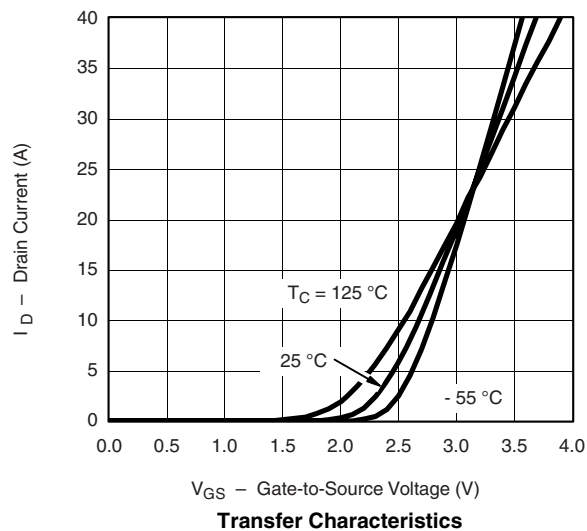
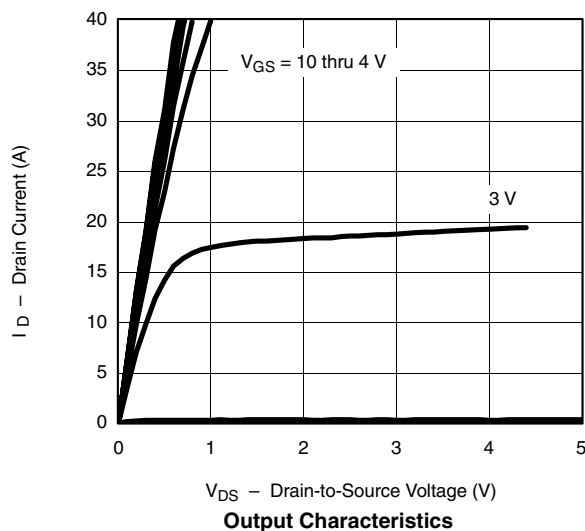
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless noted



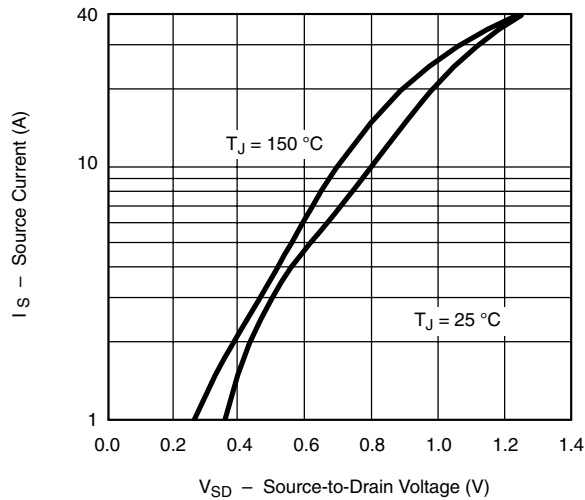
Normalized Thermal Transient Impedance, Junction-to-Ambient



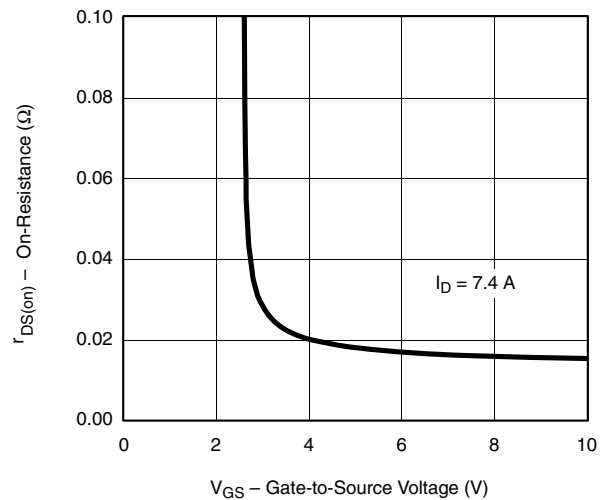
Normalized Thermal Transient Impedance, Junction-to-Foot

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless noted

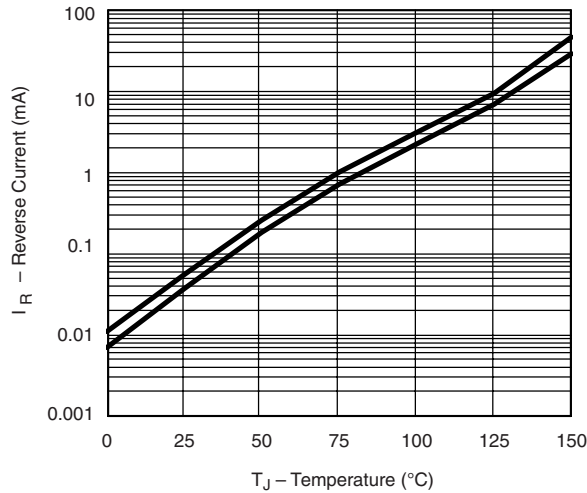
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless noted



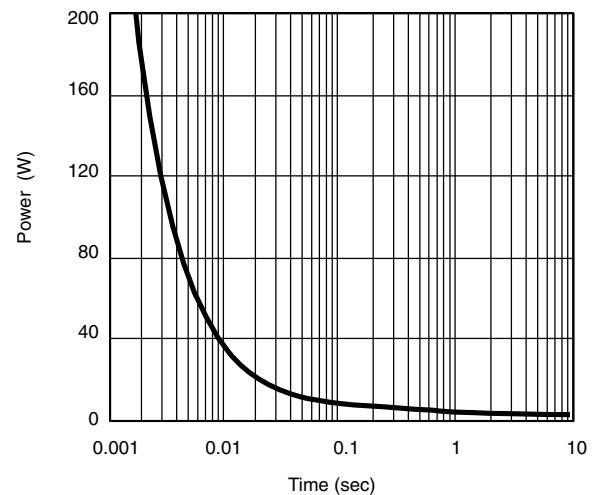
Source-Drain Diode Forward Voltage



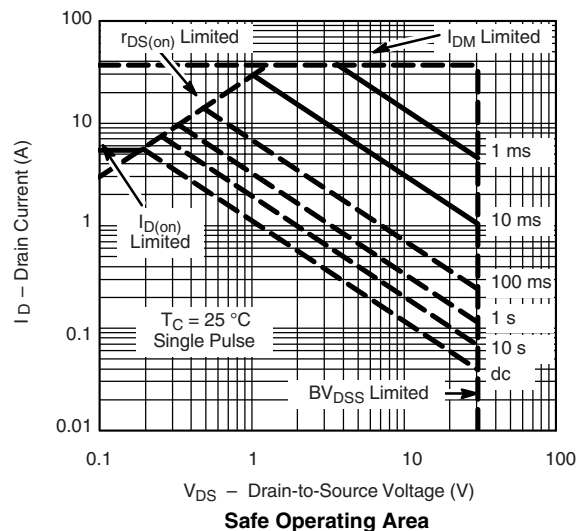
On-Resistance vs. Gate-to-Source Voltage

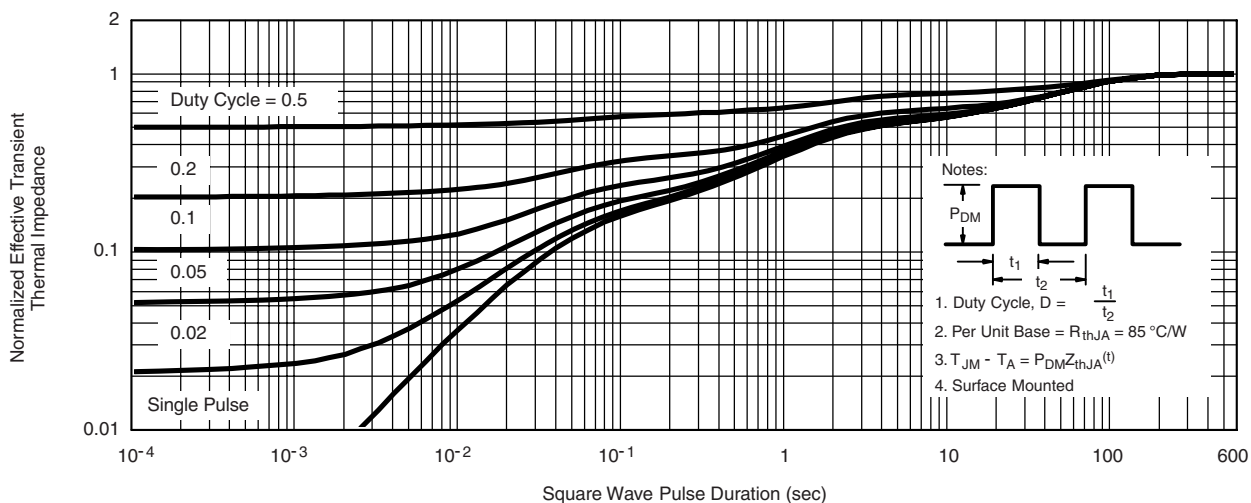
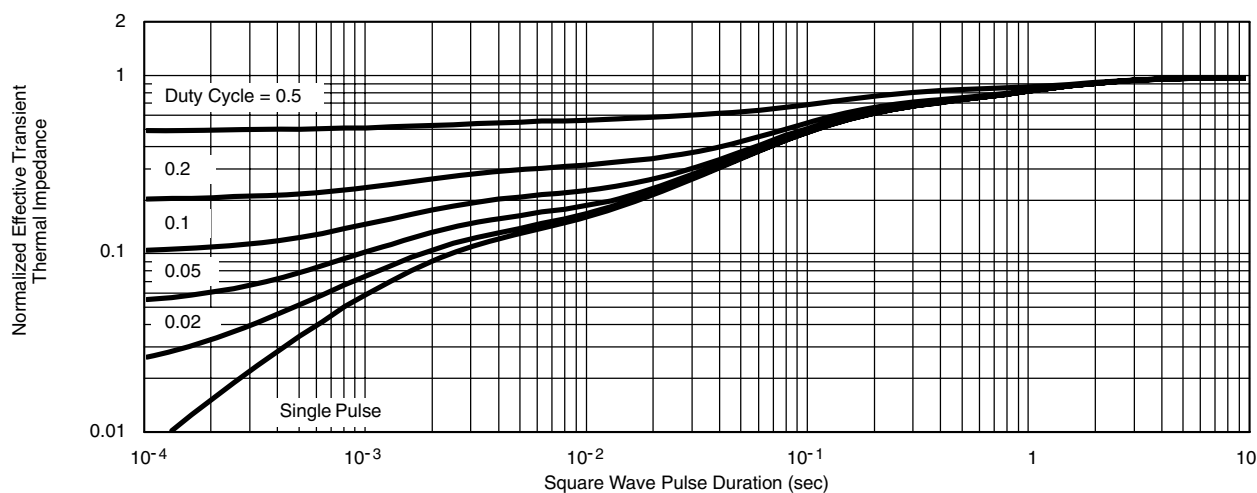


Reverse Current vs. Junction Temperature



Single Pulse Power, Junction-to-Ambient



CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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